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April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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MOS FIELD EFFECT TRANSISTOR

μ PA1808

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1808 is a switching device, which can be driven directly by a 4.0 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as DC/DC converters and power management of notebook computers and so on.

FEATURES

- 4.0 V drive available
- · Low on-state resistance

 $R_{DS(on)1} = 17 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 10 \text{ V, ID} = 5.0 \text{ A)}$

 $R_{DS(on)2} = 23 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.5 \text{ V, ID} = 5.0 \text{ A)}$

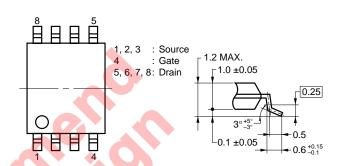
 $R_{DS(on)3} = 26 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.0 \text{ V, Ip} = 5.0 \text{ A)}$

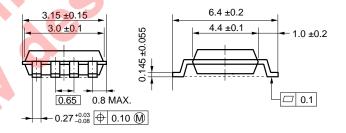
· Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1808GR-9JG	Power TSSOP8

PACKAGE DRAWING (Unit: mm)

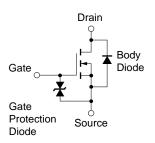




ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (Vps = 0 V)	Vgss	ID(DC) ±9.5	
Drain Current (DC) (T _A = 25°C)	ID(DC)	±9.5	Α
Drain Current (pulse) Note1	ID(pulse)	±38	Α
Total Power Dissipation Note2	Рт	2.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

EQUIVALENT CIRCUIT



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 2. Mounted on ceramic substrate of 5000 mm² x 1.1 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

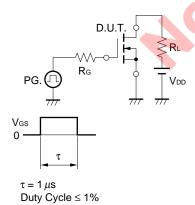
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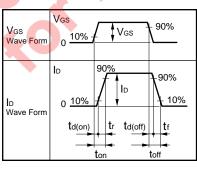


ELECTRICAL CHARACTERISTICS (TA = 25°C)

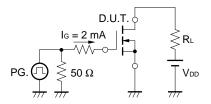
		,				
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = 30 V, V _{GS} = 0 V			1.0	μΑ
Gate Leakage Current	lgss	Vgs = ±18 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	1.5	1.9	2.5	V
Forward Transfer Admittance	y fs	V _{DS} = 10 V, I _D = 5.0 A	5.0	10.5		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, ID = 5.0 A		13.5	17	mΩ
	RDS(on)2	Vgs = 4.5 V, ID = 5.0 A		17	23	mΩ
	RDS(on)3	Vgs = 4.0 V, ID = 5.0 A		19	26	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		660		pF
Output Capacitance	Coss	VGS = 0 V		280		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		100		pF
Turn-on Delay Time	td(on)	V _{DD} = 15 V, I _D = 5.0 A		13.5		ns
Rise Time	tr	V _G s = 10 V		5.6		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		38		ns
Fall Time	t _f			7.9		ns
Total Gate Charge	Q _G	V _{DD} = 24 V	ク	13		nC
Gate to Source Charge	Qgs	V _G s = 10 V		1.8		nC
Gate to Drain Charge	Q _{GD}	I _D = 9.5 A		3.7		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 9.5 A, V _{GS} = 0 V		0.84		V
Reverse Recovery Time	trr	I _F = 9.5 A, V _{GS} = 0 V		27		ns
Reverse Recovery Charge	Qm	di/dt = 100 A/μs		19		nC

TEST CIRCUIT 1 SWITCHING TIME





TEST CIRCUIT 2 GATE CHARGE

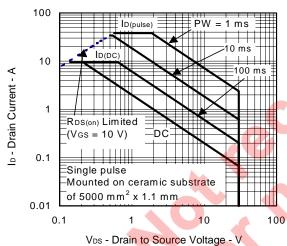


TYPICAL CHARACTERISTICS (TA = 25°C)

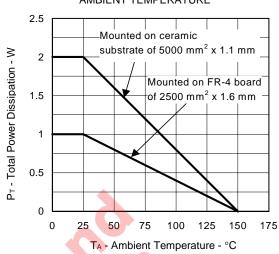
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA 120 dT - Percentage of Rated Power - % 100 80 60 40 20 0 0 25 50 75 100 125 150 175

FORWARD BIAS SAFE OPERATING AREA

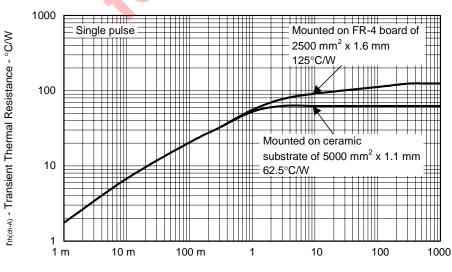
TA - Ambient Temperature - °C



TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



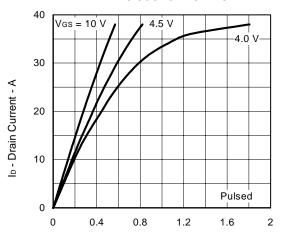
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



PW - Pulse Width - s

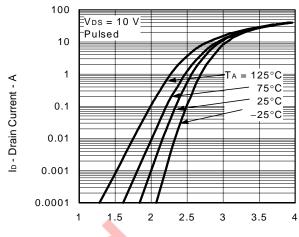
3

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



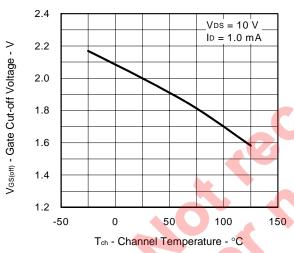
V_{DS} - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS

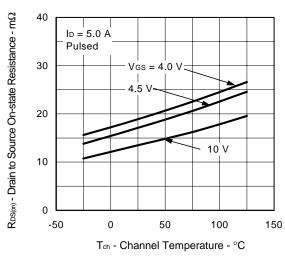


V_{GS} - Gate to Source Voltage - V

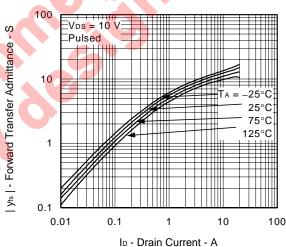
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



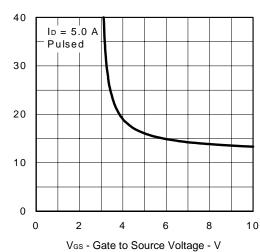
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



FORWARD TRANSFER ADMITTANCE vs. **DRAIN CURRENT**



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

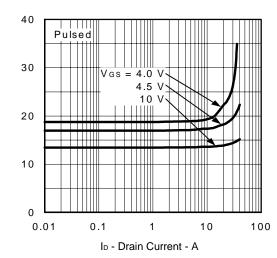


R_{DS(m)} - Drain to Source On-state Resistance - mΩ

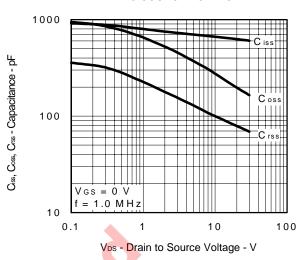
 $\mathsf{R}_{\mathsf{DS}(\mathsf{cn})}$ - Drain to Source On-state Resistance - $m\Omega$

Ves - Gate to Source Voltage - V

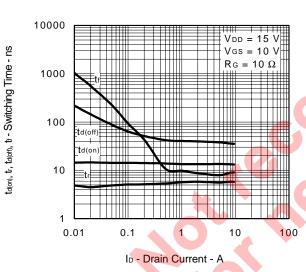
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



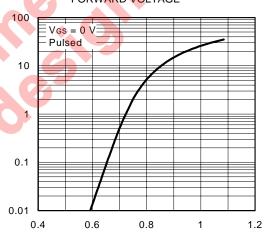
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



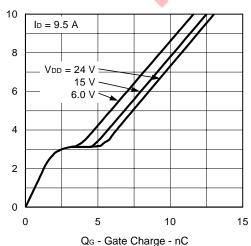
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



V_{F(S-D)} - Source to Drain Voltage - V



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

IF - Diode Forward Current - A

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